

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This triac is intended for use in motor control circuits where very high blocking voltage, high static and dynamic dV/dt as well as high dlcom/dt can occur. This "series C0" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Isolated mounting base package
- Optimized for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only
- · Very high voltage capability

3. Applications

- Compressor starting control circuits
- General purpose motor controls
- · Reversing induction motor controls e.g. vertical axis washing machines

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	1000	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	65	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	8	Α
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	5	11	35	mA





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	5	14	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \frac{\text{Fig. 7}}{}$	5	25	35	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		g
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
BTA208X-1000C0	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A					
BTA208X-1000C0/L01	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A					

7. Marking

Table 4. Marking codes

Type number	Marking code
BTA208X-1000C0	
BTA208X-1000C0/L01	BTA208X-1000C0L01

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1000	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73$ °C; Fig. 1; Fig. 2; Fig. 3	-	8	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	65	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	71	А
I ² t	I2t for fusing	t _p = 10 ms; SIN	-	21	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 12 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

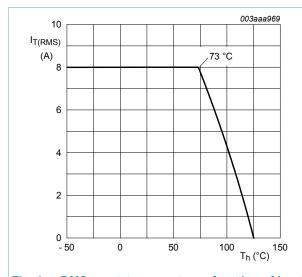


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

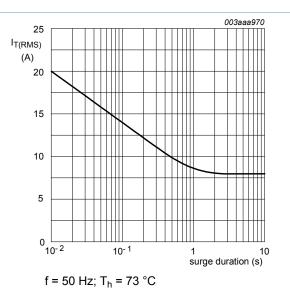


Fig. 2. RMS on-state current as a function of surge duration; maximum values

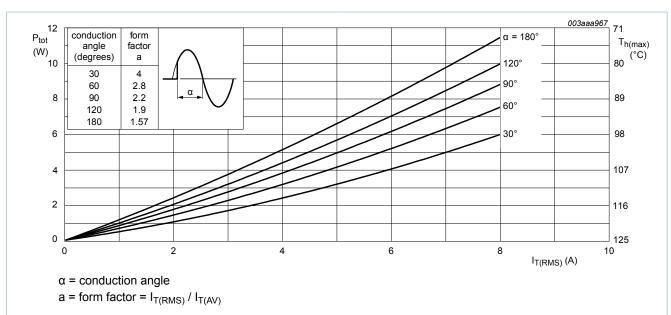


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

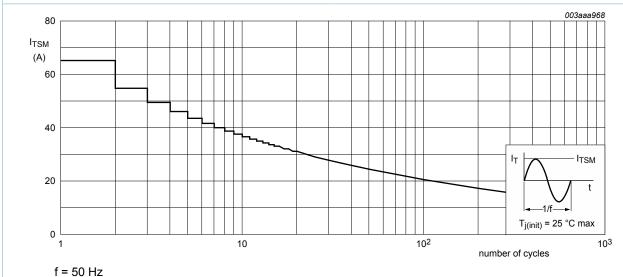
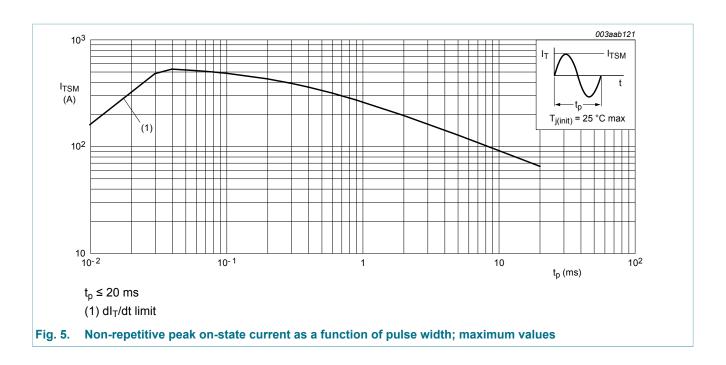


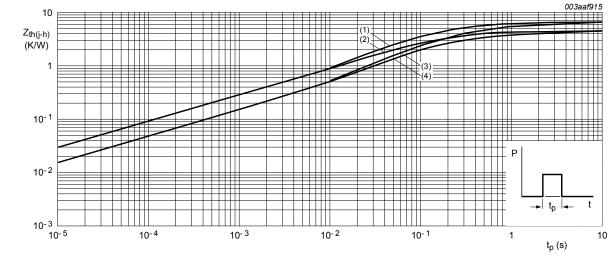
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)} thermal resistance from junction to heatsink		full cycle or half cycle; with heatsink compound; Fig. 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; Fig. 6	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	_	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

BTA208X-1000C0

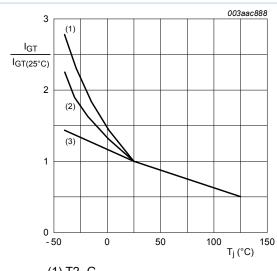
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11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	5	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	5	14	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	5	25	35	mA
I _L latching current		V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	25	50	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	48	75	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	30	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	20	50	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.25	0.4	-	V
I _D	off-state current	V _D = 1000 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics					
dV _D /dt	rate of rise of off-state voltage	5m · j · (5m				V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit; Fig. 12	12	32	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

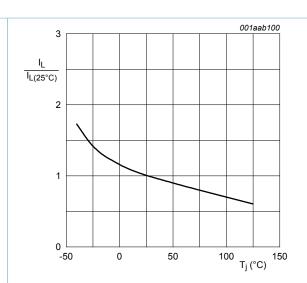


Fig. 8. Normalized latching current as a function of junction temperature

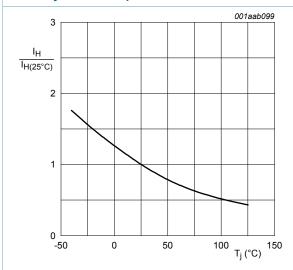
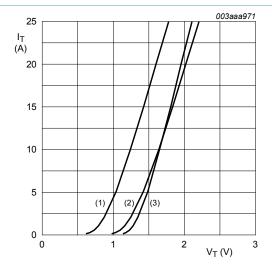
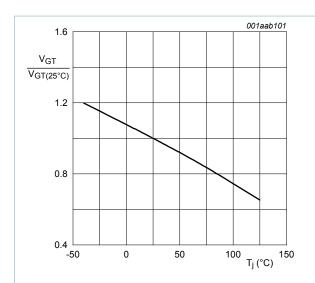


Fig. 9. Normalized holding current as a function of junction temperature

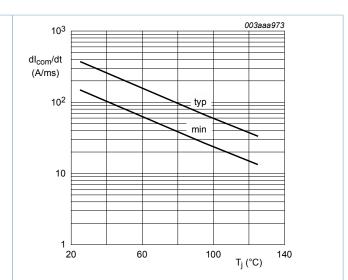


- V_o = 1.264 V; R_s = 0.0378 Ω
- (1) T_j = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

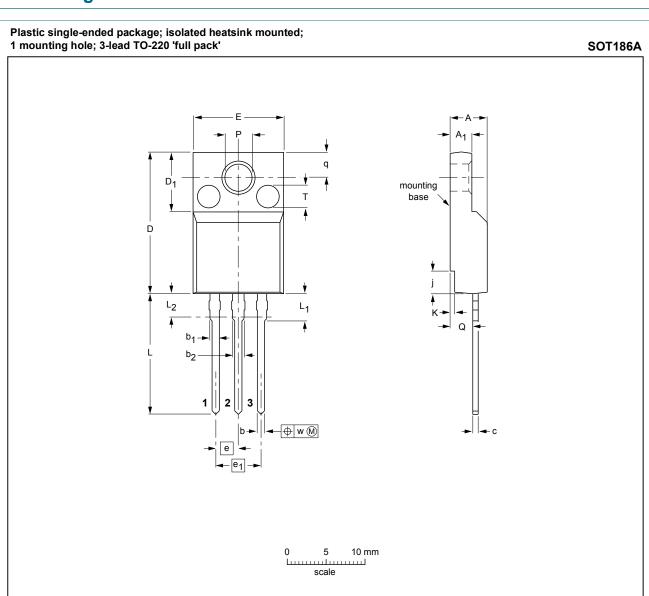






function of junction temperature; typical and minimum values

12. Package outline



DIMENSIONS (mm are the original dimensions)

UN	ГА	A	I	b	b ₁	b ₂	С	D	D ₁	E	е	e ₁	j	к	L	L ₁	L ₂ ⁽¹⁾ max.	Р	Q	q	T ⁽²⁾	w
mn	4.6 4.0	2.9 2.5	0).9).7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are # 2.5×0.8 max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	EC JEDEC JEITA			PROJECTION	ISSUE DATE
SOT186A		3-lead TO-220F				-02-04-09 06-02-14

Fig. 13. Package outline TO-220F (SOT186A)

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13. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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